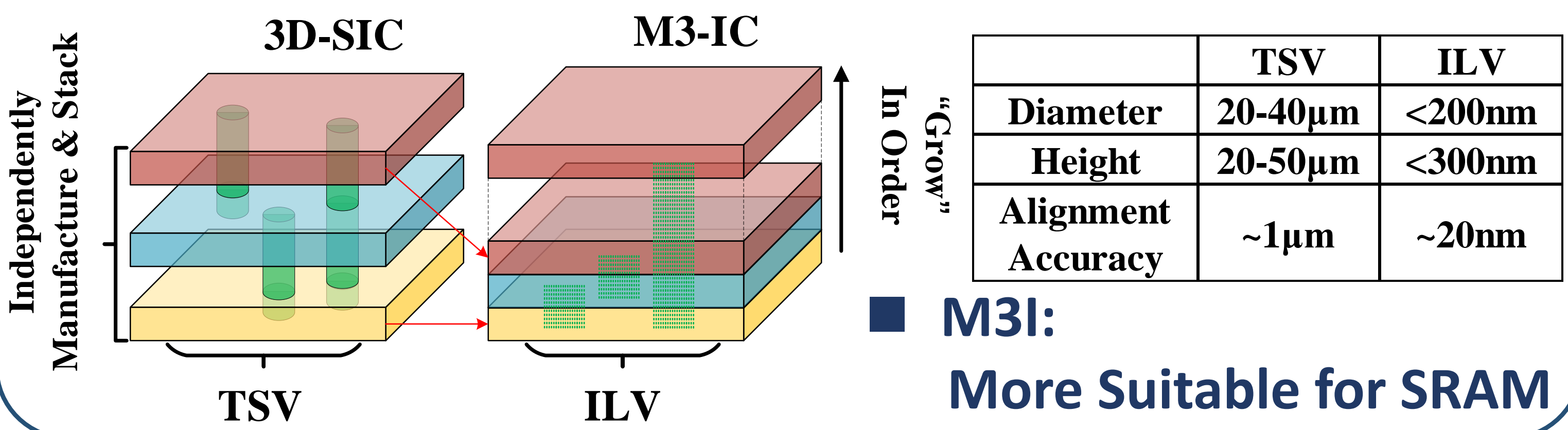


# In-growth Test for Monolithic 3D Integrated SRAM

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## Advantages of Monolithic 3D Integration



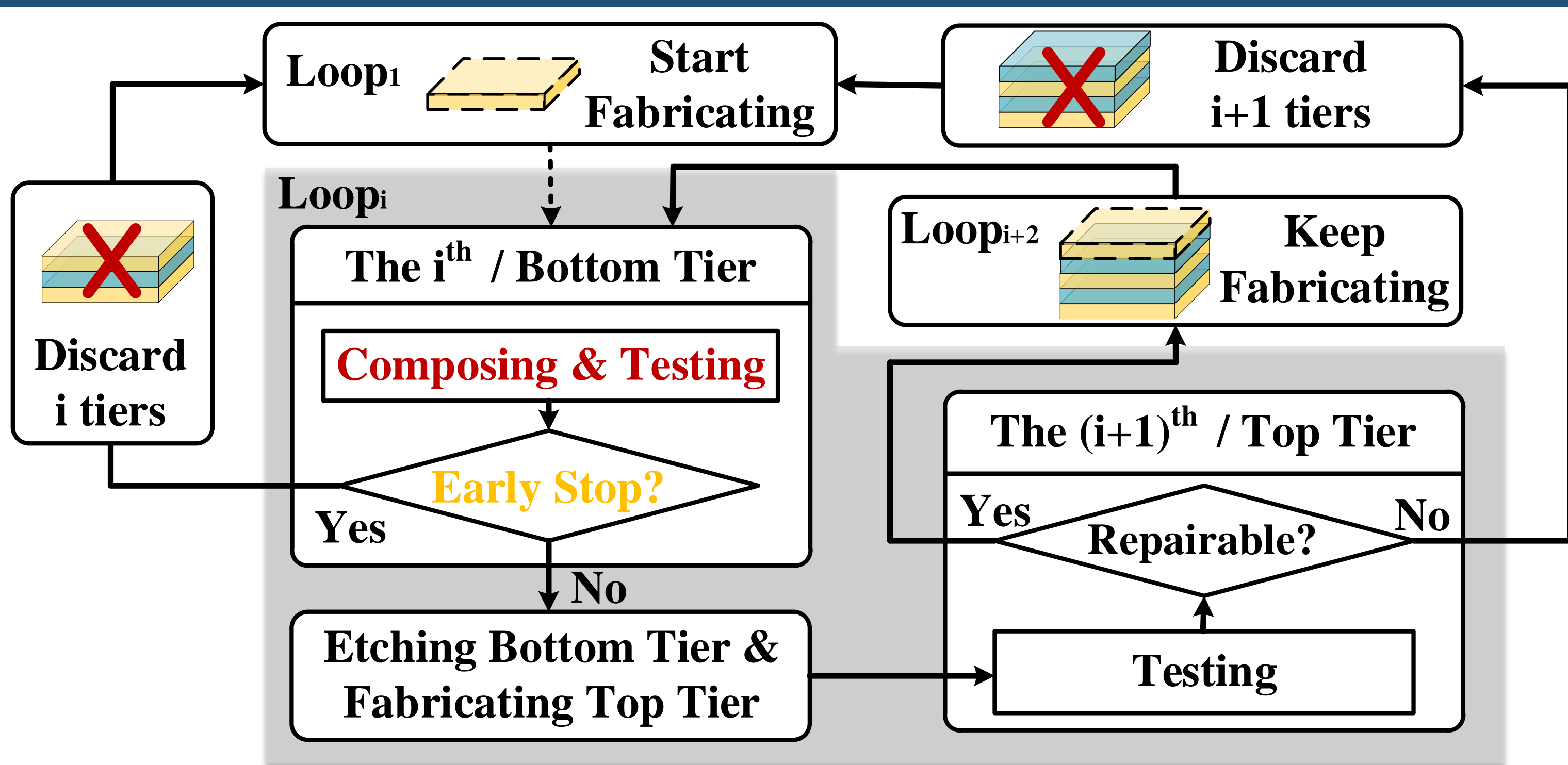
## Challenge on Test Method of M3I SRAM

### Testability Problem    Reparability Problem

- Testability Problem:**
  - Incomplete circuit components and untestable
  - Unable to adding redundant transistors.
- Reparability Problem:**
  - Unable to repair a fault cell with a redundancy cell
  - Unknown reparability before fabrication finishes

Lack of Efficient Pre-Bond Test Method & High Overall Fabrication Cost

## Overview of Proposed Test Methodology



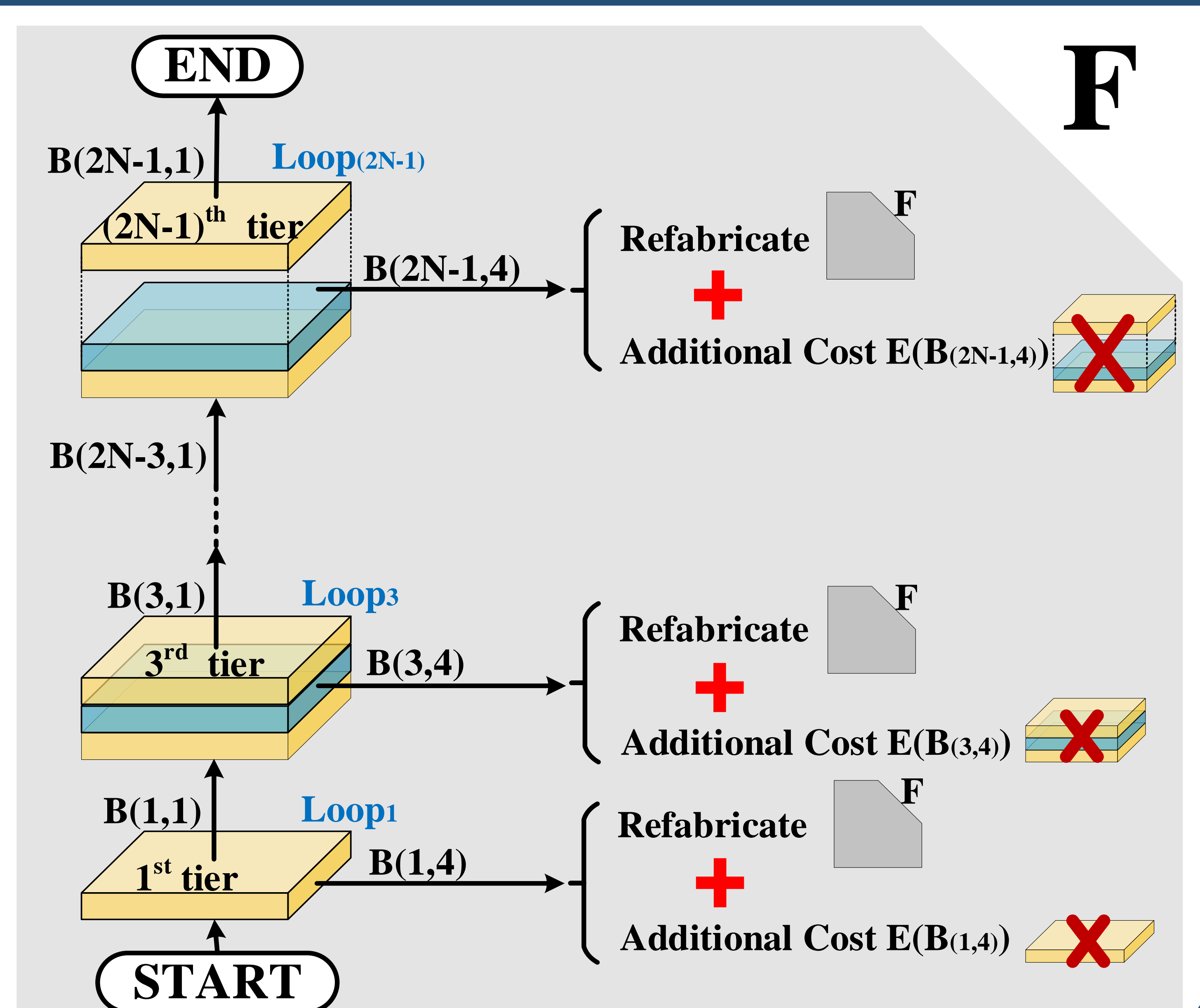
### Composing & Testing

- A novel Design-for-Testability method enables the proposed In-growth test on cell-level partitioned incomplete SRAM cells.

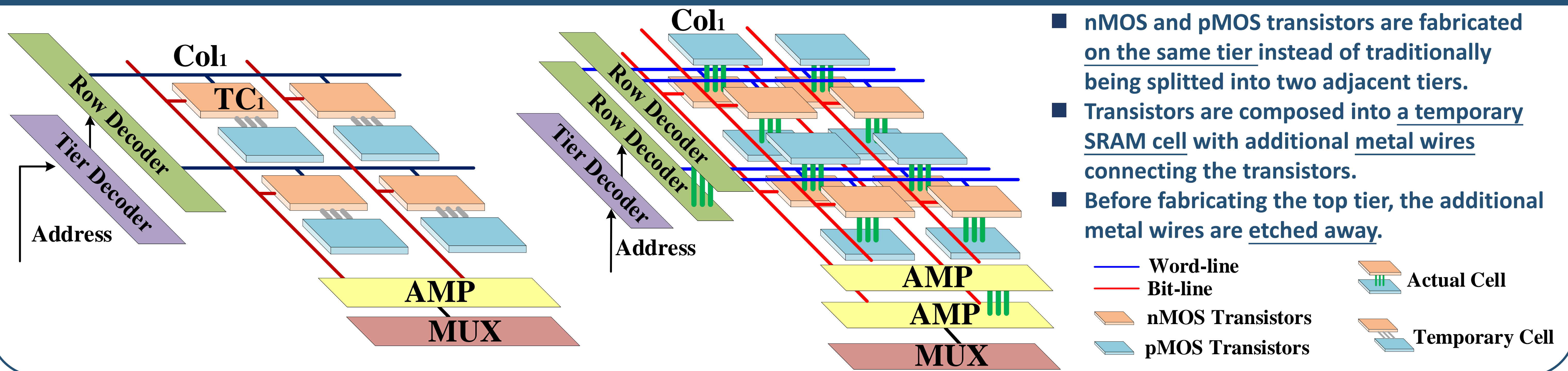
### Early Stop

- A judgement factor & a statistical cost model determine whether to stop the fabrication

## Model of Cost to Guide Early Stop



## Design-for-Testability Method to Make Incomplete SRAM Cells Testable during Fabrication



## Experiment Results: The Effectiveness & The Better Performance with More Layers

